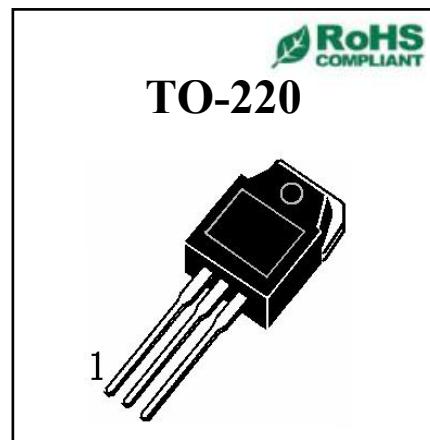


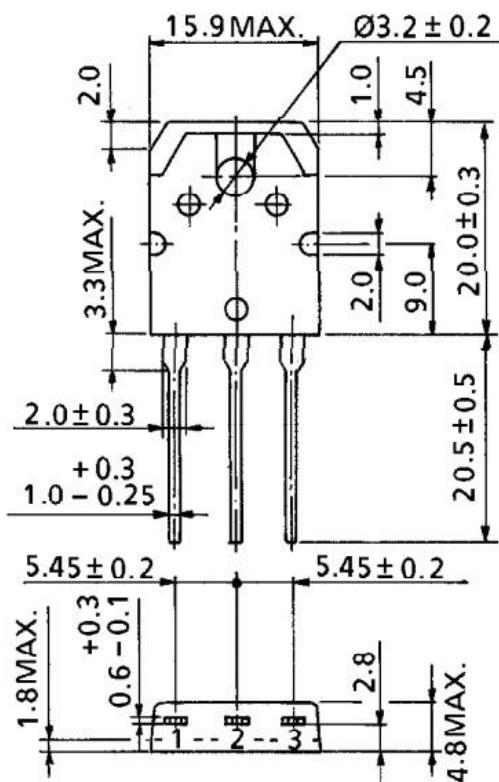
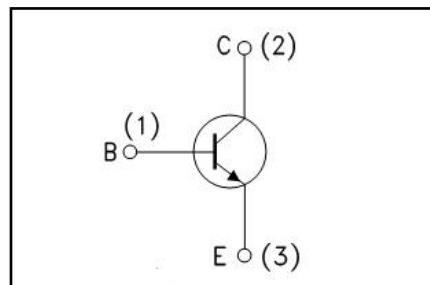
#### ◆ Features:

- ◆ High Switching Speed  
开关速度快
  - ◆ Low forward voltage drop  
正向压降低
  - ◆ High efficiency and low power loss  
高效低功耗
  - ◆ High current surge capability  
大电流浪涌能力强



## ◆ Applications

- ◆ Electronic Ballast  
电子镇流器
  - ◆ Switching Mode Power Supply  
开关电源
  - ◆ Motor Controls  
电机控制
  - ◆ Solenoid/Relay drivers and Deflection circuits applications  
电磁阀/继电器驱动器和偏转电路应用





OSA13009

High Voltage Fast-Switching NPN Power Transistor

## ◆ Absolute Maximum Ratings (Tc=25°C)

Symbol	Parameters	Ratings	Unit
VCBO	Collector-Base Voltage 集电极 - 基极电压	700	V
VCEO	Collector-Emitter Voltage 集电极 - 发射极电压	400	V
VEBO	Emitter-Base Voltage 发射极 - 基极电压	9	V
Ic	Collector Current-Continuous 集电极连续电流	12	A
IB	Base Current-Continuous 基极连续电流	6	A
PC	Collector Power Dissipation 耗散功率	130	W
Tj	Max.Operating junction temperature 最大结温	150	°C
Tstg	Storage Temperature 存储温度	-65 ~ +150	°C
θ JA	Junction to Ambient 结到环境	21	°C/W
θ JC	Junction to Case 结到外壳	1.55	°C/W



OSA13009

High Voltage Fast-Switching NPN Power Transistor

## ◆ Electrical characteristics (Tc=25°C unless otherwise noted)

Symbol	Parameters	Min	Typ	Max	Units	Conditions
I <sub>CBO</sub>	Collector Cutoff Current 集电极截止电流		--	<b>50</b>	μA	V <sub>CE</sub> =60V, I <sub>B</sub> =0
I <sub>EBO</sub>	Emitter Cutoff Current 发射极截止电流		--	<b>1</b>	mA	V <sub>EB</sub> =9V, I <sub>C</sub> =0
BV <sub>CEO</sub>	Collector Emitter Sustaining voltage(Note 1) 集电极发射极持续电压	<b>400</b>			V	I <sub>C</sub> =50mA, I <sub>B</sub> =0
V <sub>CESat</sub>	Collector Emitter Saturation Voltage(Note 1) 集电极发射极饱和电压			<b>1.2</b> <b>1.5</b> <b>3</b>	V	I <sub>C</sub> =5A, I <sub>B</sub> =1A I <sub>C</sub> =8A, I <sub>B</sub> =1.6A I <sub>C</sub> =12A, I <sub>B</sub> =3A
V <sub>BESat</sub>	Base-Emitter Saturation Voltage(Note 1) 基极发射极饱和电压			<b>1.2</b> <b>1.6</b>	V	I <sub>C</sub> =5A, I <sub>B</sub> =1A I <sub>C</sub> =8A, I <sub>B</sub> =1.6A
h <sub>FE</sub>	DC Current Gain(Note 1) 直流电流增益	<b>8</b> <b>6</b>	--	<b>40</b> <b>30</b>		I <sub>C</sub> =5A, V <sub>CE</sub> =5V I <sub>C</sub> =8A, V <sub>CE</sub> =5V
f <sub>T</sub>	Current-Gain—Bandwidth 电流增益带宽	<b>4</b>	--	--	MHz	V <sub>CE</sub> =10V, I <sub>C</sub> =0.5A, f=1MHz

Note 1: Pulse test: PW &lt;= 300us , duty cycle &lt;= 2%.

## ◆ Ratings and Characteristic curves

